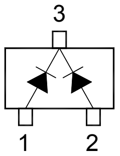
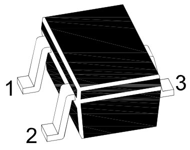
MMBD222CCE

Silicon Epitaxial Planar Switching Diode

Application

- Ultra high speed switching





SOT-523 Plastic Package
Marking Code: **N9**

Absolute Maximum Ratings (T_a = 25 °C)

Parameter	Symbol	Value	Unit
Maximum Peak Reverse Voltage	V_{RM}	80	V
Reverse Voltage	V_R	80	V
Average Forward Current	$I_{F(AV)}$	100	mA
Maximum Peak Forward Current	I_{FM}	300	mA
Non-repetitive Peak Forward Surge Current (t = 1 µs)	I_{FSM}	2	A
Power Dissipation	P_{tot}	150	mW
Junction Temperature	T_j	150	°C
Storage Temperature Range	T_{stg}	- 55 to + 150	°C

Characteristics at T_a = 25 °C

Parameter	Symbol	Min.	Max.	Unit
Forward Voltage at I_F = 100 mA	V_F	-	1.2	V
Reverse Breakdown Voltage at I_R = 100 µA	$V_{(BR)R}$	80	-	V
Reverse Current at V_R = 70 V	I_R	-	0.1	µA
Total Capacitance at V_R = 6 V, f = 1 MHz	C_{tot}	-	3.5	pF
Reverse Recovery Time at V_R = 6 V, I_F = 5 mA, I_{rr} = 0.1 I_R , R_L = 100 Ω	t_{rr}	-	4	ns

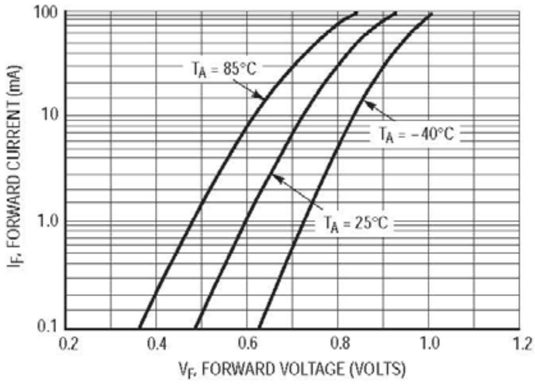


Figure 1. Forward Voltage

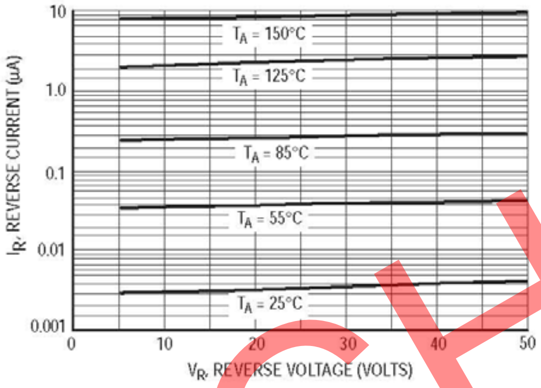


Figure 2. Reverse Current

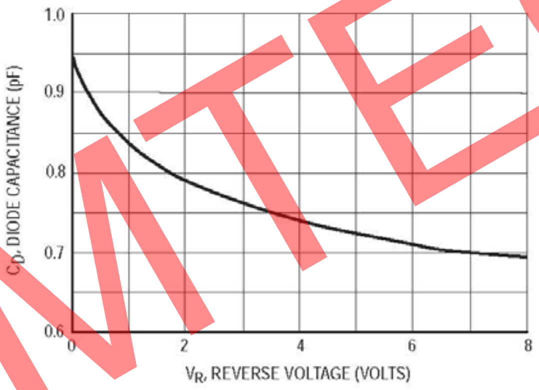


Figure 3. Diode Capacitance